

Molding Type Module IGBT, 1-in-1 Package, 1200 V and 600 A



Double INT-A-PAK

PRODUCT SUMMARY						
V _{CES}	1200 V					
I _C at T _C = 80 °C	600 A					
$V_{CE(on)}$ (typical) at $I_C = 600 \text{ A}, 25 \text{ °C}$	1.9 V					
Speed	8 kHz to 30 kHz					
Package	Double INT-A-PAK					
Circuit	Single switch with AP diode					

FEATURES

- High short circuit capability, self limiting to 6 x I_C
- 10 µs short circuit capability
- ROHS
- V_{CE(on)} with positive temperature coefficient
- Low inductance case
- · Fast and soft reverse recovery antiparallel FWD
- Isolated copper baseplate using DCB (Direct Copper Bonding) technology
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- · AC inverter drives
- Switching mode power supplies
- Electronic welder at fsw up to 20 kHz

DESCRIPTION

Vishay's IGBT power module provides ultralow conduction loss as well as short circuit ruggedness. It is designed for applications such as inverters and UPS.

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Collector to emitter voltage	V _{CES}		1200	V	
Gate to emitter voltage	V_{GES}		± 20	V	
Collector oursent at T 150 °C			910		
Collector current at T _J = 150 °C	I _C	T _C = 80 °C	600		
Pulsed collector current	I _{CM} ⁽¹⁾	T _C = 80 °C	1200	А	
Diode continuous forward current	I _F		600		
Diode maximum forward current	I _{FM}		1200		
Maximum power dissipation	P _D	T _J = 150 °C	3125	W	
Short circuit withstand time	t _{SC}	T _J = 125 °C	10	μs	
RMS isolation voltage	V _{ISOL}	f = 50 Hz, t = 1 min	2500	V	
I ² t-value, diode	l ² t	$V_R = 0 \text{ V}, t = 10 \text{ ms}, T_J = 125 ^{\circ}\text{C}$	74 000	A ² s	

Note

⁽¹⁾ Repetitive rating: pulse width limited by maximum junction temperature.



IGBT ELECTRICAL SPECIFICATIONS (T _C = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	V _{(BR)CES}	T _J = 25 °C	1200	-	-	
Collector to emitter voltage	V _{CE(on)}	$V_{GE} = 15 \text{ V}, I_{C} = 600 \text{ A}, T_{J} = 25 ^{\circ}\text{C}$	-	1.9	-	
Collector to enfitter voltage		V _{GE} = 15 V, I _C = 600 A, T _J = 125 °C	-	2.1	-	ľ
Gate to emitter threshold voltage	V _{GE(th)}	$V_{CE} = V_{GE}$, $I_C = 24$ mA, $T_J = 25$ °C	5.0	6.2	7.0	
Collector cut-off current	I _{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0$ V, $T_{J} = 25$ °C	-	-	5.0	mA
Gate to emitter leakage current	I _{GES}	$V_{GE} = V_{GES}$, $V_{CE} = 0$ V, $T_{J} = 25$ °C	=	=	400	nA

SWITCHING CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-on delay time	t _{d(on)}		-	200	-	
Rise time	t _r		-	62	-	ns mJ
Turn-off delay time	t _{d(off)}	$V_{CC} = 600 \text{ V}, I_{C} = 600 \text{ A}, R_{g} = 3 \Omega,$	-	510	-	
Fall time	t _f	V _{GE} = ± 15 V, T _J = 25 °C	-	60	-	
Turn-on switching loss	E _{on}		-	39	-	
Turn-off switching loss	E _{off}		-	48	-	
Turn-on delay time	t _{d(on)}		-	210	-	ns
Rise time	t _r		-	65	-	
Turn-off delay time	t _{d(off)}	$V_{CC} = 600 \text{ V}, I_{C} = 600 \text{ A}, R_{g} = 3 \Omega,$ $V_{GE} = \pm 15 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	600	-	
Fall time	t _f		-	75	-	
Turn-on switching loss	E _{on}		-	45	-	I
Turn-off switching loss	E _{off}		-	60	-	mJ
Input capacitance	C _{ies}		-	41.0	-	
Output capacitance	C _{oes}	V _{GE} = 0 V, V _{CE} = 25 V, f = 1.0 MHz	-	3.1	-	nF
Reverse transfer capacitance	C _{res}		-	2.0	-	
SC data	I _{SC}	$t_{SC} \leq 10 \; \mu s, V_{GE} = 15 \; V, T_J = 25 \; ^{\circ}C, \\ V_{CC} = 900 \; V, V_{CEM} \leq 1200 \; V$	-	2600	-	Α
Stray inductance	L _{CE}		-	-	20	nΗ
Module lead resistance, terminal to chip	R _{CC'+EE'}	T _C = 25 °C	-	0.18	-	mΩ

DIODE ELECTRICAL SPECIFICATIONS (T _C = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Diode forward voltage	V _F	_F I _F = 600 A	$T_J = 25 ^{\circ}C$	-	1.8	2.4	V
blode forward voltage			$T_J = 125 ^{\circ}\text{C}$	-	1.9	ı	
Diode reverse recovery charge	Q _{rr}		$T_J = 25 ^{\circ}C$	-	65	-	μC
Diode reverse recovery charge			T _J = 125 °C	-	100	-	μΟ
Diode peak reverse recovery current	I _{rr}	$I_{rr} \qquad I_{F} = 600 \text{ A, } V_{R} = 600 \text{ V,}$ $dI_{F}/dt = -6000 \text{ A/}\mu\text{s,}$ $V_{GE} = -15 \text{ V}$ E_{rec}	$T_J = 25 ^{\circ}C$	-	450	-	Α
Diode peak reverse recovery current			T _J = 125 °C	-	510	-	_ ^
Diada vayawa vaaayan, anavay	E _{rec}		T _J = 25 °C	-	35	-	m l
Diode reverse recovery energy			T _J = 125 °C	-	42	-	mJ



THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating temperature range		TJ		-40	-	150	°C
Storage temperature range		T _{Stg}		-40	-	125	°C
Junction to case	IGBT	Б		-	-	0.04	
per module	Diode	R _{thJC}		-	-	0.09	K/W
Case to sink		R _{thCS}	Conductive grease applied	-	0.035	-	
Mounting torque			Power terminal screw: M6	2.5 to 5.0		Nm	
			Mounting screw: M6	3.0 to 6.0		INIII	
Weight				310		g	

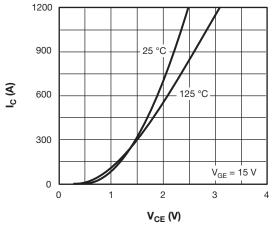


Fig. 1 - Typical Output Characteristics

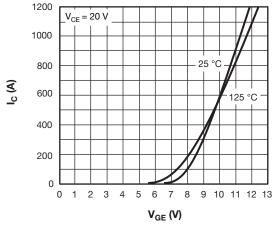


Fig. 2 - Typical Transfer Characteristics

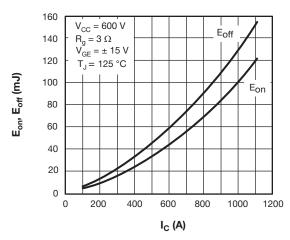


Fig. 3 - Switching Loss vs. Collector Current

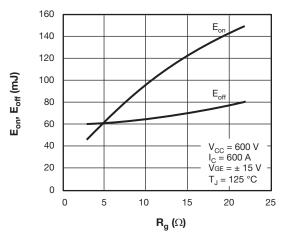


Fig. 4 - Switching Loss vs. Gate Resistor



 10^{2}

10¹

10⁰

10

C (nF)

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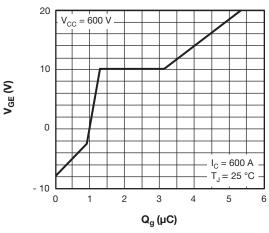


Fig. 5 - Gate Charge Characteristics



 V_{CE} (V) Fig. 6 - Typical Capacitance vs. Collector-Emitter Voltage

20

25

30

15

10

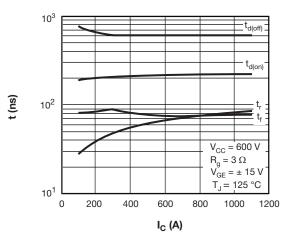


Fig. 7 - Typical Switching Times

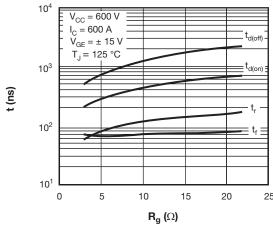


Fig. 8 - Typical Switching Times vs. Gate Resistance Ra

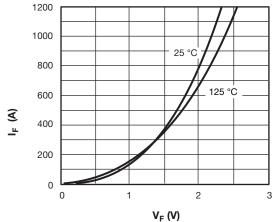


Fig. 9 - Typical forward Characteristics (Diode)

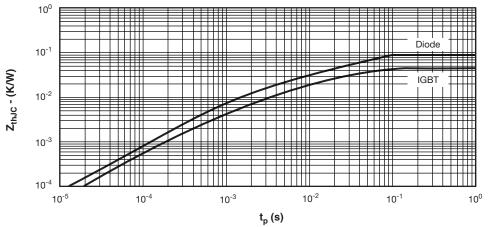
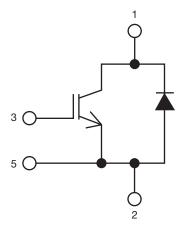


Fig. 10 - Transient Thermal Impedance

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95526			



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